

## Excellent Integrated System Limited

Stocking Distributor

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[Vishay Semiconductor/Diodes Division](#)  
[UHF20FCT-E3/4W](#)

For any questions, you can email us directly:

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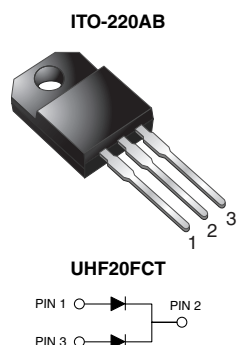


**New Product**

**UHF20FCT**

Vishay General Semiconductor

## Dual Common-Cathode Ultrafast Recovery Rectifier



### FEATURES

- Oxide planar chip junction
- Ultrafast recovery times
- Soft recovery characteristics
- Low switching losses, high efficiency
- High forward surge capability
- Solder dip 260 °C, 40 s
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



**RoHS**  
COMPLIANT

### TYPICAL APPLICATIONS

For use in high frequency power factor correctors, switching mode power supplies, freewheeling diodes and secondary dc-to-dc rectification application.

### MECHANICAL DATA

**Case:** ITO-220AB

Epoxy meets UL 94V-0 flammability rating

**Terminals:** Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test

**Polarity:** As marked

**Mounting Torque:** 10 in-lbs maximum

### PRIMARY CHARACTERISTICS

$I_{F(peak)}$	10 A x 2
$V_{RRM}$	300 V
$I_{FSM}$	180 A
$t_{rr}$	25 ns
$V_F$ at $I_F = 10$ A	0.85 V
$T_J$ max.	175 °C

### MAXIMUM RATINGS ( $T_A = 25$ °C unless otherwise noted)

PARAMETER	SYMBOL	UHF20FCT	UNIT
Maximum repetitive peak reverse voltage	$V_{RRM}$	300	V
Maximum DC working forward current per device at $T_C = 125$ °C	$I_{F(peak)}$	20 10	A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	$I_{FSM}$	180	A
Isolation voltage (ITO-220AB only) from terminal to heatsink $t = 1$ min	$V_{AC}$	1500	V
Operating junction and storage temperature range	$T_J, T_{STG}$	- 55 to + 175	°C

### ELECTRICAL CHARACTERISTICS ( $T_A = 25$ °C unless otherwise noted)

PARAMETER	TEST CONDITIONS	SYMBOL	TYP.	MAX.	UNIT
Maximum instantaneous forward voltage per diode <sup>(1)</sup>	$I_F = 5.0$ A $I_F = 10.0$ A $T_A = 25$ °C	$V_F$	0.96 1.02	- 1.20	V
	$I_F = 5.0$ A $I_F = 10.0$ A $T_A = 125$ °C		0.77 0.85	- -	
Maximum reverse current per diode <sup>(2)</sup>	$V_R = 300$ V $T_A = 25$ °C $T_A = 125$ °C	$I_R$	0.06 25	5 150	μA

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<b>ELECTRICAL CHARACTERISTICS</b> ( $T_A = 25^\circ\text{C}$ unless otherwise noted)					
PARAMETER	TEST CONDITIONS	SYMBOL	TYP.	MAX.	UNIT
Maximum reverse recovery time	$I_F = 0.5\text{ A}$ , $I_R = 1.0\text{ A}$ , $I_{rr} = 0.25\text{ A}$	$t_{rr}$	20	25	ns
Maximum reverse recovery time per diode	$I_F = 1.0\text{ A}$ , $dI/dt = 50\text{ A}/\mu\text{s}$ , $V_R = 30\text{ V}$ , $I_{rr} = 0.1 I_{RM}$	$t_{rr}$	28	35	ns
Typical softness factor (tb/ta)	$I_F = 10\text{ A}$ , $dI/dt = 200\text{ A}/\mu\text{s}$ , $V_R = 200\text{ V}$ , $T_J = 125^\circ\text{C}$ per diode	S	0.36	-	-
Typical reverse recovery current		$I_{RM}$	7.0	-	A
Typical stored charge		$Q_{rr}$	160	-	nC
Typical forward recovery time per diode	$I_F = 10\text{ A}$ , $dI/dt = 80\text{ A}/\mu\text{s}$ , $V_{FR} = 1.1 \times V_{Fmax}$	$t_{fr}$	150	-	ns

**Notes:**

(1) Pulse test: 300  $\mu\text{s}$  pulse width, 1 % duty cycle

(2) Pulse test: Pulse width  $\leq 40\text{ ms}$

<b>THERMAL CHARACTERISTICS</b> ( $T_A = 25^\circ\text{C}$ unless otherwise noted)			
PARAMETER	SYMBOL	UHF20FCT	UNIT
Typical thermal resistance per diode	$R_{\theta JA}^{(1)}$	50	$^\circ\text{C}/\text{W}$
	$R_{\theta JC}^{(2)}$	4.6	

**Notes:**

(1) Without heatsink, free air

(2) With infinite heatsink

<b>ORDERING INFORMATION</b> (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
ITO-220AB	UHF20FCT-E3/4W	1.74	4W	50/tube	Tube

**RATINGS AND CHARACTERISTICS CURVES**

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

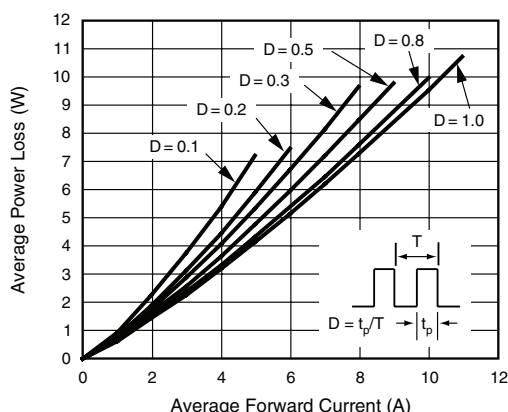


Figure 1. Forward Power Loss Characteristics Per Diode

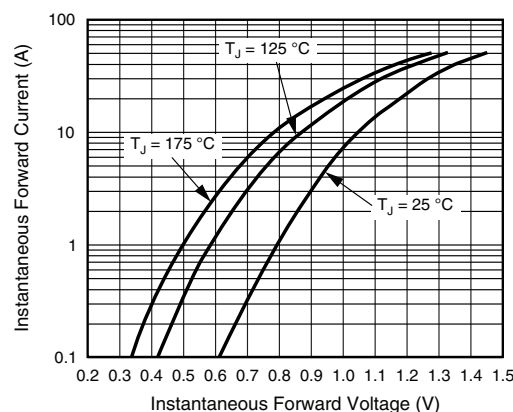


Figure 2. Typical Instantaneous Forward Characteristics Per Diode



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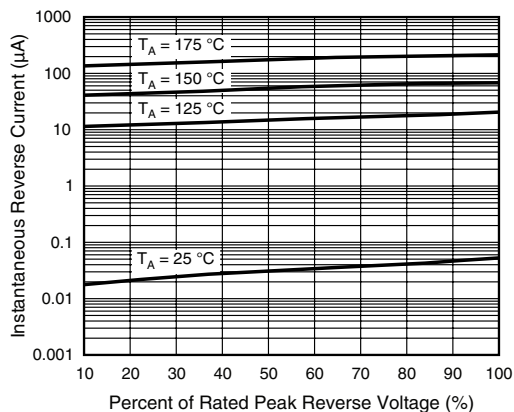


Figure 3. Typical Reverse Leakage Characteristics Per Diode

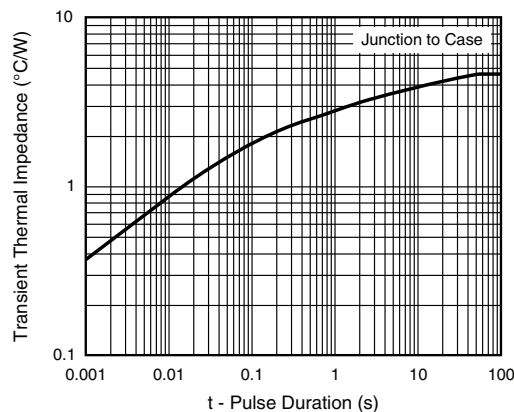


Figure 5. Typical Transient Thermal Impedance Per Diode

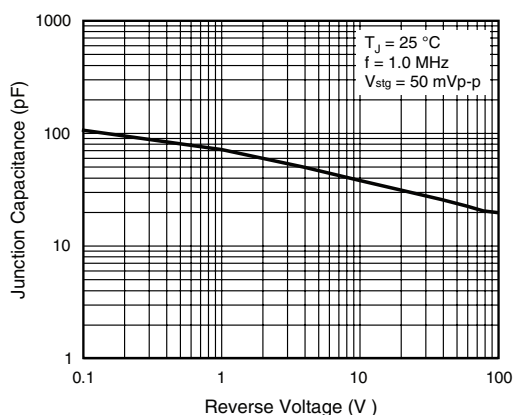
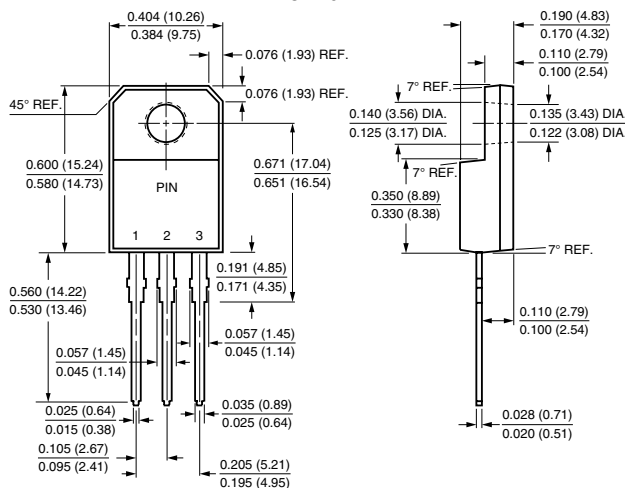


Figure 4. Typical Junction Capacitance Per Diode

## PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

### ITO-220AB





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